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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

FAX RECEIVED  
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GROUP 1700

Applicant: Steinmann et al

Art Unit: 1765

Serial No.: 09/852,921

Examiner: Deo, D.

Filing Date: 05/10/01

Docket No.: TI-29881

Title: METHOD OF INTEGRATING A THIN FILM RESISTOR IN A  
MULTI-LEVEL METAL TUNGSTEN-PLUG INTERCONNECTAmendment under 37 CFR 1.115

Assistant Commissioner of Patents

Washington, DC 20231

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 08/13/02. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

In the Claims:

Amend Claim 1 to read as follows:

- Sub C.  
B1
1. (amended) A method of fabricating an integrated circuit, comprising the steps of:
- forming a first interlevel dielectric over a semiconductor body;
  - forming a layer of resistor material over said first interlevel dielectric layer;
  - forming a metal stack on said layer of resistor material;
  - forming a first pattern over said metal stack;